

PRELIMINARY DATASHEET

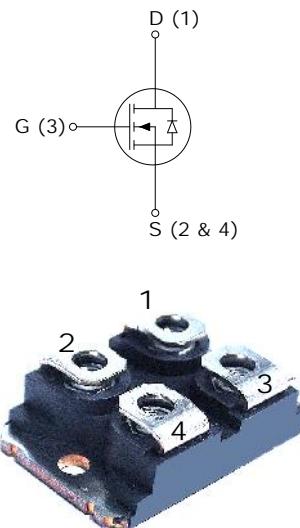
**600V, 39A N-Channel Enhancement mode CoolMOS™
Power MOSFET in Isolated SOT227 Package**

APPLICATIONS

- PC power supplies
- Consumer SMPS
- Telecom power supplies
- Server power supplies
- Solar inverters
- Welding inverters
- Induction heating
- Electronics ballast

FEATURES

- Extreme dv/dt rated
- Ultra low gate charge
- Ultra low effective capacitances
- Low R_{d(on)} <0.07Ω
- Pb-free finished; **RoHS compliant**



MAXIMUM RATINGS, at $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Units
Drain - Source Voltage	V_{DSS}	600	V
Drain current – continuous $T_C = 25^\circ\text{C}$	I_D	39	A
$T_C = 100^\circ\text{C}$		24	
Drain current – pulsed, pulse width limited by T_{jmax}	$I_{D,pulse}$	117	
Inverse diode continuous forward current $T_C = 25^\circ\text{C}$	I_S	39	
Inverse diode direct current, pulse width limited by T_{jmax}	I_{SM}	117	
Drain source voltage slope $V_{DS} = 480\text{V}, I_D = 47\text{A}, T_j = 125^\circ\text{C}$	dv/dt	50	V/ns
Gate source voltage Static AC ($f > 1\text{Hz}$)	V_{GS}	± 20 ± 30	V
Soldering temperature, wave soldering 1.6 mm (0.063 in) from case for 10 s	T_{sold}	260	°C
Operating junction and storage temperature	T_j, T_{stg}	-55... +150	°C

Thermal and Isolation Characteristics

Parameter	Symbol	Max. Value	Units
Characteristics			
Thermal resistance, junction to case	R_{thJC}	0.44	K /W
Thermal resistance, junction to ambient	R_{thJA}	62	
Isolation voltage, RMS (measured between terminals and mounting base, 50-60 Hz, for 1-3 seconds)	V_{iso}	3000	V

Electrical Characteristics, at $T_C = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 0.25\text{mA}$	600	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 2.7\text{mA}$	2.1	3.0	3.9	
Drain-source diode forward voltage	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_{\text{F}} = I_{\text{S}} = 39\text{A}$	-	-	1.2	V
Zero gate voltage drain current	I_{DSS}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 600\text{V}$ $T_C = 25^\circ\text{C}$ $T_C = 150^\circ\text{C}$	-	0.5	25 250	μA
Gate-body leakage current, forward	I_{GSS}	$V_{\text{GS}} = 30\text{V}, V_{\text{DS}} = 0\text{V}$	-	-	100	nA
Static drain-source On-resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 30\text{ A}$ $T_C = 25^\circ\text{C}$ $T_C = 150^\circ\text{C}$	-	0.06 0.16	0.07	Ω
Gate resistance	R_G	f=1MHz, open drain	-	0.62	-	Ω
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{\text{DS}} = 25\text{V},$ $V_{\text{GS}} = 0\text{V},$ f = 1MHz	-	6800	-	pF
Output capacitance	C_{oss}		-	2200	-	
Reverse transfer capacitance	C_{rss}		-	145	-	

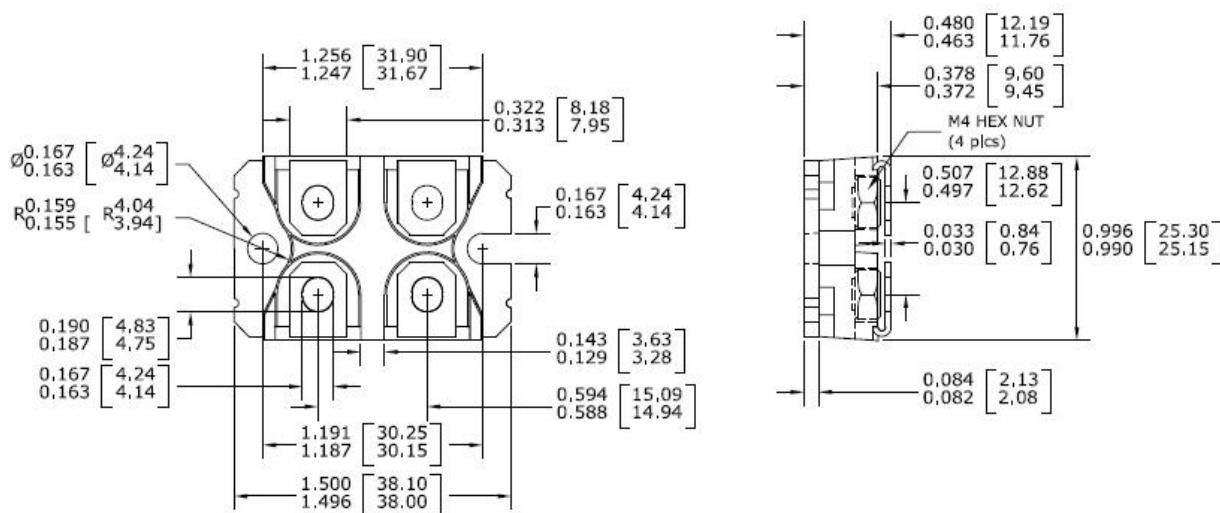
Switching Characteristics, at $T_C = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Turn-on delay time	$t_{\text{d(on)}}$	$V_{\text{DS}}=380\text{V}, I_{\text{D}} = 39\text{ A},$ $V_{\text{GS}}=0/13\text{V}, R_G = 1.8\Omega$ $T_C = 125^\circ\text{C}$	-	15	-	ns
Rise time	t_r		-	22	-	
Turn-off delay time	$t_{\text{d(off)}}$		-	92	-	
Fall time	t_f		-	7	-	
Gate charge	Q_g	$V_{\text{DD}}=350\text{V}, I_{\text{D}} = 39\text{A}$ $V_{\text{GS}} = 0 \text{ to } 10\text{V}$	-	252	-	nC
Gate-source charge	Q_{gs}		-	24	-	
Gate-drain charge	Q_{gd}		-	121	-	

Drain-Source Diode Characteristics, at $T_C = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Reverse recovery time	t_{rr}	$V_{\text{R}}=350\text{V}, I_{\text{s}} = I_{\text{F}} = 39\text{A}$ $dI_{\text{F}}/dt = 100\text{A}/\mu\text{s}$	-	482	-	ns
Reverse recovery charge	Q_{rr}		-	19	-	
Peak reverse recovery current	I_{rrm}		-	61	-	

Package Outline Drawing



CoolMOS™ is a registered trademark of Infineon Technologies AG.

CAUTION: These devices are ESD sensitive. Use proper handling procedure.

Disclaimer

These specifications may not be considered as a guarantee of components characteristics. Components have to be tested depending on intended application as adjustments may be necessary. The use of **iQXPRZ Power Inc.** components in life support appliances and systems are subject to written approval of **iQXPRZ Power Inc.**